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<ul> <li>Members of the Texas Instruments Widebus<sup>™</sup> Family</li> </ul>	SN54LVTH16541 WD PACKAGE SN74LVTH16541 DGG OR DL PACKAGE (TOP VIEW)
<ul> <li>State-of-the-Art Advanced BiCMOS Technology (ABT) Design for 3.3-V Operation and Low Static-Power Dissipation</li> </ul>	$1 \overline{OE1} \begin{bmatrix} 1 & 48 \\ 1 & 48 \end{bmatrix} 1 \overline{OE2} \\ 1Y1 \begin{bmatrix} 2 & 47 \\ 1Y2 \end{bmatrix} 1A1 \\ 1Y2 \begin{bmatrix} 3 & 46 \end{bmatrix} 1A2$
<ul> <li>Support Mixed-Mode Signal Operation (5-V Input and Output Voltages With 3.3-V V<sub>CC</sub>)</li> </ul>	GND 4 45 GND 1Y3 5 44 1A3 1Y4 6 43 1A4
<ul> <li>Support Unregulated Battery Operation Down to 2.7 V</li> </ul>	V <sub>CC</sub>
<ul> <li>Typical V<sub>OLP</sub> (Output Ground Bounce)</li> <li>&lt; 0.8 V at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C</li> </ul>	1Y6 9 40 1A6 GND 10 39 GND
<ul> <li>I<sub>off</sub> and Power-Up 3-State Support Hot Insertion</li> </ul>	1Y7   11 38   1A7 1Y8   12 37   1A8
<ul> <li>Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors</li> </ul>	2Y1 13 36 2A1 2Y2 14 35 2A2 GND 15 34 GND
<ul> <li>Distributed V<sub>CC</sub> and GND Pin Configuration Minimizes High-Speed Switching Noise</li> </ul>	2Y3   16 33   2A3 2Y4   17 32   2A4 V <sub>CC</sub>   18 31   V <sub>CC</sub>
<ul> <li>Flow-Through Architecture Optimizes PCB Layout</li> </ul>	2Y5 [ 19 30 ] 2A5 2Y6 [ 20 29 ] 2A6
<ul> <li>Latch-Up Performance Exceeds 500 mA Per JESD 17</li> </ul>	GND
<ul> <li>ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V</li> </ul>	2Y8 23 26 2A8 2OE1 24 25 2OE2

 Using Machine Model (C = 200 pF, R = 0)
 Package Options Include Plastic Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings

### description

These 16-bit buffers/drivers are designed specifically for low-voltage (3.3-V)  $V_{CC}$  operation, but with the capability to provide a TTL interface to a 5-V system environment.

These devices are noninverting 16-bit buffers composed of two 8-bit sections with separate output-enable signals. For either 8-bit buffer section, the two output-enable ( $1\overline{OE1}$  and  $1\overline{OE2}$  or  $2\overline{OE1}$  and  $2\overline{OE2}$ ) inputs must be low for the corresponding Y outputs to be active. If either output-enable input is high, the outputs of that 8-bit buffer section are in the high-impedance state.

When  $V_{CC}$  is between 0 and 1.5 V, the devices are in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V,  $\overline{OE}$  should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.



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### description (continued)

These devices are fully specified for hot-insertion applications using I<sub>off</sub> and power-up 3-state. The I<sub>off</sub> circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict.

The SN54LVTH16541 is characterized for operation over the full military temperature range of  $-55^{\circ}$ C to  $125^{\circ}$ C. The SN74LVTH16541 is characterized for operation from  $-40^{\circ}$ C to  $85^{\circ}$ C.

FUNCTION TABLE (each 8-bit section)										
INPUTS OUTPUT										
OE1	OE2	Α	Y							
L	L	L	L							
L	L	Н	Н							
Н	Х	Х	Z							
Х	Н	Х	Z							

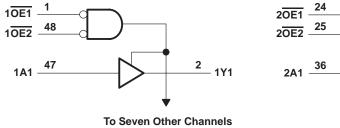
# logic symbol<sup>†</sup>

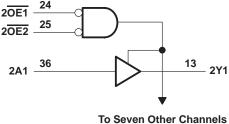
10E1	1	&			
10E2	48		EN1		
20E1	24	&			
20E1 20E2	25	ũ	EN2		
2022					
1A1	47		1 ⊽	2	4.1/4
1A1	46	'		3	1Y1
	44			5	1Y2
1A3	43			6	1Y3
1A4	41			8	1Y4
1A5	40			9	1Y5
1A6	38			11	1Y6
1A7	37			12	1Y7
1A8	36			13	1Y8
2A1	35	1	I 2 ▽	14	2Y1
2A2	33			16	2Y2
2A3	32			17	2Y3
2A4	30			19	2Y4
2A5	29			20	2Y5
2A6	27			22	2Y6
2A7	26			23	2Y7
2A8					2Y8

<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



# logic diagram (positive logic)





# absolute maximum ratings over operating free-air temperature range (unless otherwise noted)<sup>†</sup>

Supply voltage range, V <sub>CC</sub> Input voltage range, V <sub>I</sub> (see Note 1)	
Voltage range applied to any output in the high-impedance	
or power-off state, V <sub>O</sub> (see Note 1)	
Voltage range applied to any output in the high state, V <sub>O</sub> (see Note 1)	-0.5 V to V <sub>CC</sub> + 0.5 V
Current into any output in the low state, I <sub>O</sub> : SN54LVTH16541	
SN74LVTH16541	
Current into any output in the high state, IO (see Note 2): SN54LVTH16541 .	
SN74LVTH16541 .	64 mA
Input clamp current, I <sub>IK</sub> (V <sub>I</sub> < 0)	–50 mA
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0)	
Package thermal impedance, $\theta_{JA}$ (see Note 3): DGG package	
DL package	
Storage temperature range, T <sub>stg</sub>	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. This current flows only when the output is in the high state and  $V_{O} > V_{CC}$ .

3. The package thermal impedance is calculated in accordance with JESD 51.

### recommended operating conditions (see Note 4)

			SN54LVTI	H16541	SN74LVTI	UNIT	
			MIN	MAX	MIN	MAX	UNIT
VCC	Supply voltage	2.7	3.6	2.7	3.6	V	
VIH	High-level input voltage	2	Ŵ	2		V	
VIL	Low-level input voltage		\$0.8		0.8	V	
VI	Input voltage	4	5.5		5.5	V	
ЮН	High-level output current	6	24		-32	mA	
IOL	Low-level output current	201	48		64	mA	
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled	00	10		10	ns/V
Δt/ΔV <sub>CC</sub>	Power-up ramp rate	Q 200		200		μs/V	
ТА	Operating free-air temperature	-55	125	-40	85	°C	

NOTE 4: All unused control inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



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# electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS			4LVTH16	6541	SN74	LINUT					
PAI	RAMEIER	TEST CONDITIONS			TYP†	MAX	MIN TYP <sup>†</sup>		MAX	UNIT			
Vik		V <sub>CC</sub> = 2.7 V,	lj = -18 mA			-1.2			-1.2	V			
		V <sub>CC</sub> = 2.7 V to 3.6 V,	I <sub>OH</sub> = -100 μA	V <sub>CC</sub> -0	.2		V <sub>CC</sub> -0.	2					
<b>M</b> =		V <sub>CC</sub> = 2.7 V,	I <sub>OH</sub> = –8 mA	2.4			2.4			V			
VOH		V = = = 2 V	I <sub>OH</sub> = -24 mA	2						v			
		V <sub>CC</sub> = 3 V	I <sub>OH</sub> = -32 mA				2						
		V <sub>CC</sub> = 2.7 V	I <sub>OL</sub> = 100 μA			0.2			0.2				
		$v_{CC} = 2.7 v$	I <sub>OL</sub> = 24 mA			0.5			0.5				
Val			I <sub>OL</sub> = 16 mA			0.4			0.4	V			
VOL			I <sub>OL</sub> = 32 mA			0.5			0.5	v			
		$V_{CC} = 3 V$	I <sub>OL</sub> = 48 mA			0.55							
			I <sub>OL</sub> = 64 mA						0.55				
		V <sub>CC</sub> = 0 or 3.6 V,	V <sub>I</sub> = 5.5 V			10			10				
Control inputs	V <sub>CC</sub> = 3.6 V,	$V_{I} = V_{CC} \text{ or } GND$			±1			±1	]				
		V <sub>CC</sub> = 3.6 V	$V_I = V_{CC}$		1	<u>(</u> 1			1	μA			
	Data inputs		V <sub>I</sub> = 0		2E	-5			-5	-5			
loff	off $V_{CC} = 0$ ,		$V_{I} \text{ or } V_{O} = 0 \text{ to } 4.5 \text{ V}$		Q				±100	μA			
	Data inputs	V <sub>CC</sub> = 3 V	V <sub>I</sub> = 0.8 V	75	5		75						
14			V <sub>I</sub> = 2 V	-75	2		-75			μΑ			
l(hold)		V <sub>CC</sub> = 3.6 V <sup>‡</sup> ,	V <sub>I</sub> = 0 to 3.6 V	d'd					500 -750	μΛ			
IOZH	-	V <sub>CC</sub> = 3.6 V,	V <sub>O</sub> = 3 V			5			5	μA			
IOZL		V <sub>CC</sub> = 3.6 V,	V <sub>O</sub> = 0.5 V			-5			-5	μA			
I <sub>OZPU</sub>		$\frac{V_{CC}}{OE} = 0$ to 1.5 V, V <sub>O</sub> = OE = don't care	0.5 V to 3 V,			±100*			±100	μA			
I <sub>OZPD</sub>		$\frac{V_{CC}}{OE}$ = 1.5 V to 0, V <sub>O</sub> = OE = don't care	: 0.5 V to 3 V,			±100*			±100	μA			
Icc		V <sub>CC</sub> = 3.6 V,	Outputs high			0.19			0.19				
		$V_{\rm OC} = 3.6 \text{ v},$ $I_{\rm O} = 0,$	Outputs low	5				mA					
		$V_{I} = V_{CC} \text{ or } GND$	Outputs disabled			0.19			0.19	,			
∆I <sub>CC</sub> §		$V_{CC} = 3 V$ to 3.6 V, On Other inputs at $V_{CC}$ or				0.2			0.2	mA			
Ci		V <sub>I</sub> = 3 V or 0			4			4		pF			
Co		V <sub>O</sub> = 3 V or 0			9			9		pF			

\* On products compliant to MIL-PRF-38535, this parameter is not production tested.

<sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .

<sup>‡</sup>This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.

§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V<sub>CC</sub> or GND.



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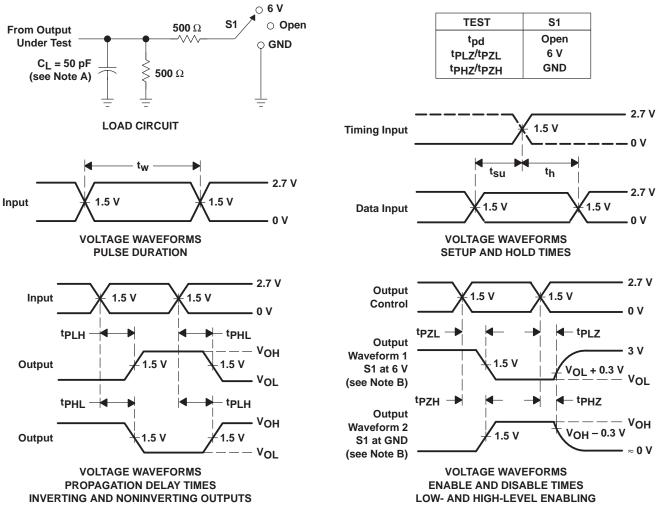
# switching characteristics over recommended operating free-air temperature range, CL = 50 pF (unless otherwise noted) (see Figure 1)

			5	SN54LV	<b>FH16541</b>			SN74	LVTH1	6541		
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 3.3 V ± 0.3 V				V <sub>CC</sub> = 3.3 V ± 0.3 V			V <sub>CC</sub> = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	MIN	TYP†	MAX	MIN	MAX	
<sup>t</sup> PLH	А	Y	1	3.7	4	4	1	2.4	3.5		3.8	ns
<sup>t</sup> PHL	~	I	1	3.7	JIL	4	1	2	3.5		3.8	115
<sup>t</sup> PZH	OE	Y	1.1	4.8	PE PE	5.7	1.2	2.7	4.6		5.5	ns
<sup>t</sup> PZL	OE	T	1.1	4.8	Y ,	5.4	1.2	2.8	4.6		5.2	115
<sup>t</sup> PHZ	OE	×	2.1	6.2		6.5	2.2	4.1	5.9		6.2	20
<sup>t</sup> PLZ		ſ	1.9	5.7		6	2.2	3.8	5.4		5.5	ns
<sup>t</sup> sk(o)				2					0.5		0.5	ns

<sup>†</sup> All typical values are at  $V_{CC}$  = 3.3 V,  $T_A$  = 25°C.



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### PARAMETER MEASUREMENT INFORMATION

NOTES: A. C<sub>1</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>f</sub>  $\leq$  2.5 ns, t<sub>f</sub>  $\leq$  2.5 ns. D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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